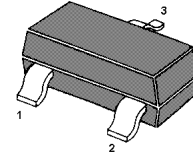
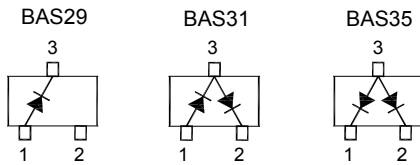


BAS29 BAS31 BAS35

Silicon Epitaxial Planar Switching Diodes



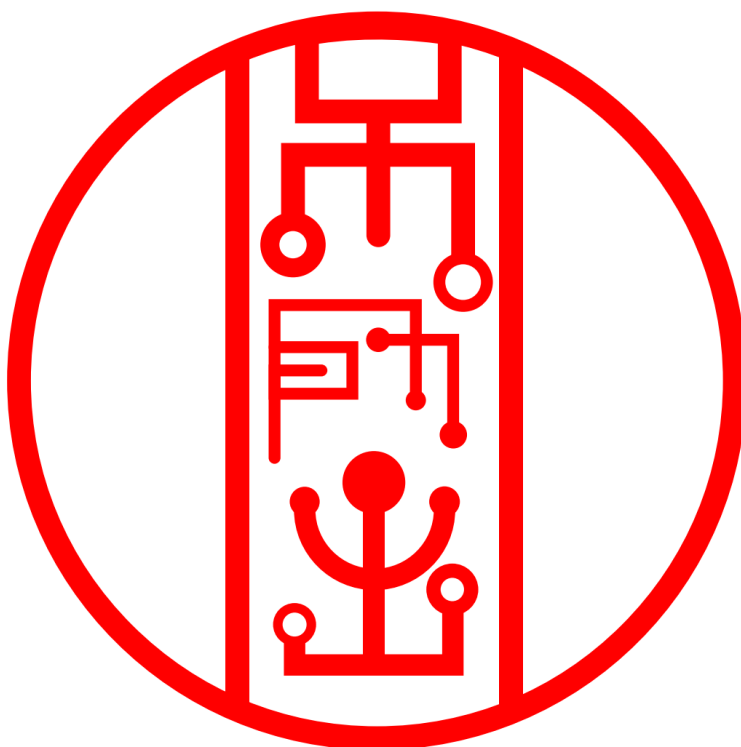
BAS29 Marking Code: **L20**
BAS31 Marking Code: **L21**
BAS35 Marking Code: **L22**
SOT-23 Plastic Package

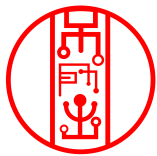
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	120	V
Maximum Average Forward Current	$I_{F(AV)}$	200	mA
Repetitive Peak Forward Current	I_{FRM}	600	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	2 1	A
	$t = 1 \mu\text{s}$ $t = 1 \text{ s}$		
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage				
at $I_F = 10 \text{ mA}$	V_F	-	750	mV
at $I_F = 50 \text{ mA}$	V_F	-	840	mV
at $I_F = 100 \text{ mA}$	V_F	-	900	mV
at $I_F = 200 \text{ mA}$	V_F	-	1	V
at $I_F = 400 \text{ mA}$	V_F	-	1.25	V
Reverse Current				
at $V_R = 90 \text{ V}$	I_R	-	100	nA
at $V_R = 90 \text{ V}$, $T_J = 150^\circ\text{C}$	I_R	-	100	μA
Reverse Breakdown Voltage	$V_{(BR)R}$	120	-	V
at $I_R = 1 \text{ mA}$				
Total Capacitance	C_T	-	35	pF
at $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$				
Reverse Recovery Time	t_{rr}	-	50	ns
at $I_F = I_R = 10 \text{ mA}$, $I_{rr} = 1 \text{ mA}$, $R_L = 100 \Omega$				



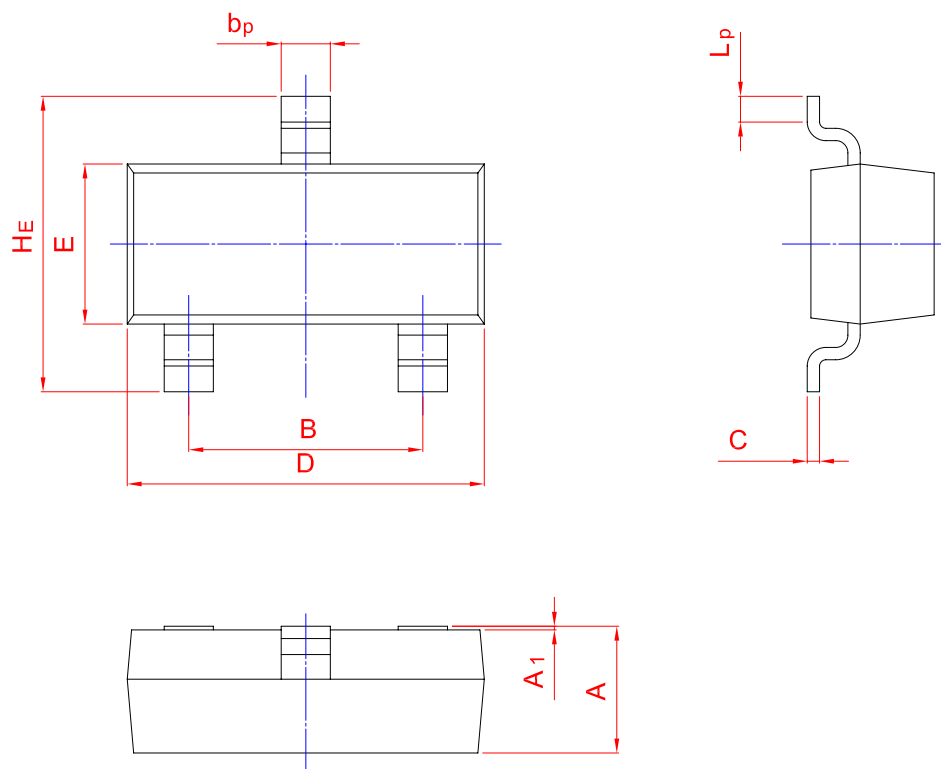


BAS29 BAS31 BAS35

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20